

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	600	V	
	V _{DSX}	600	V	V _{GS} =-30V
Continuous drain current	I _D	±16	A	
Pulsed drain current	I _{D(puls)}	±64	A	
Gate-source voltage	V _{GS}	±30	V	
Repetitive or non-repetitive	I _{AR}	16	A	T _{ch} ≤150°C
Maximum avalanche energy	E _{AS}	242.7	mJ	*1
Maximum drain-source dV/dt	dV _{DS} /dt	20	kV/μs	V _{DS} ≤600V
Peak diode recovery dV/dt	dV/dt	5	kV/μs	*2
Max. power dissipation	P _D	2.16	W	T _a =25°C
		97		T _c =25°C
Operating and storage temperature range	T _{ch}	+150	°C	
	T _{stg}	-55 to +150	°C	
Isolation voltage	V _{ISO}	2	kVrms	t=60sec, f=60Hz

*1 L=1.74mH, V_{CC}=60V, See to Avalanche Energy Graph

*2 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C

Electrical characteristics (T_c=25°C unless otherwise specified)

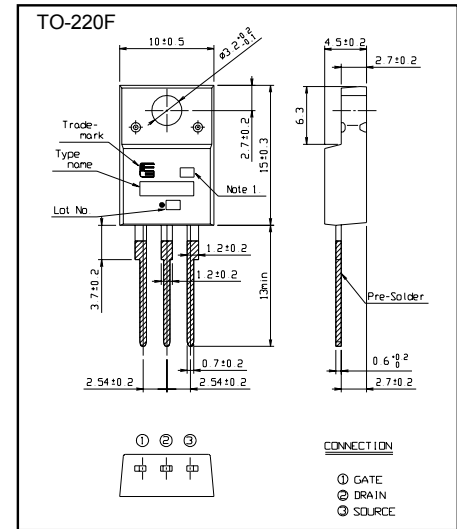
Item	Symbol	Test Conditions			
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =250μA V _{GS} =0V	600		V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0	5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =600V V _{GS} =0V T _{ch} =25°C		25	μA
		V _{DS} =480V V _{GS} =0V T _{ch} =125°C		250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V	10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =8A V _{GS} =10V	0.42	0.57	Ω
Forward transconductance	g _{fs}	I _D =8A V _{DS} =25V	6.5	13	S
Input capacitance	C _{iss}	V _{DS} =25V	1590	2390	pF
Output capacitance	C _{oss}	V _{GS} =0V	200	300	
Reverse transfer capacitance	C _{rss}	f=1MHz	11	17	
Turn-on time t _{on}	td(on)	V _{CC} =300V I _D =8A	29	43.5	ns
	t _r	V _{GS} =10V	16	24	
Turn-off time t _{off}	td(off)	R _{GS} =10 Ω	58	87	
	t _f		8	12	
Total Gate Charge	Q _G	V _{CC} =300V	34	51	nC
Gate-Source Charge	Q _{GS}	I _D =16A	12	18	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V	10	15	
Avalanche capability	I _{AV}	L=1.74mH T _{ch} =25°C	16		A
Diode forward on-voltage	V _{SD}	I _F =16A V _{GS} =0V T _{ch} =25°C	1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =16A V _{GS} =0V	0.68		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C	7.8		μC

Thermal characteristics

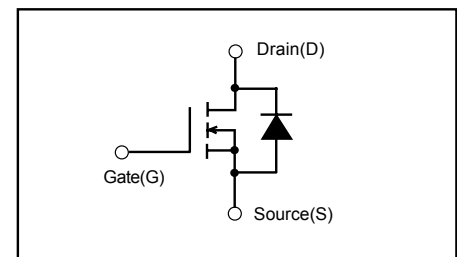
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			1.289	°C/W
	R _{th(ch-a)}	channel to ambient			58.0	°C/W

<http://www.fujielectric.co.jp/fdt/scd/>

Outline Drawings [mm]



Equivalent circuit schematic



Characteristics

